

HF/VHF power transistor

BLW86

Description:

N-P-N silicon planar epitaxial transistor intended for use in class-A, AB and B operated HF and VHF transmitters with a nominal supply voltage of 28 V. The transistor is resistance stabilized and is guaranteed to withstand severe load mismatch conditions.

Features:

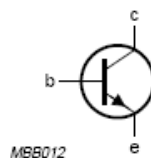
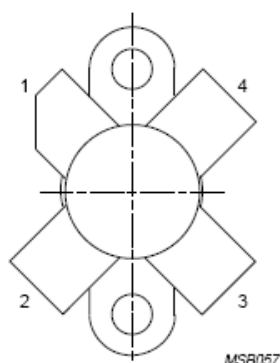
It has a 3/8" flange envelope with a ceramic cap. All leads are isolated from the flange.

Data:

MODE OF OPERATION	V _{CE} V	f MHz	P _L W	G _p dB	η %	\bar{z}_i Ω	\bar{Y}_L mS	d ₃ dB
c.w. (class-B)	28	175	45	> 7,5	> 70	0,7 + j1,3	110 - j62	-
s.s.b. (class-AB)	28	1,6 - 28	5-47,5 (P.E.P.)	typ. 19	typ. 45	-	-	typ. -30
s.s.b. (class-A)	26	1,6 - 28	17 (P.E.P.)	typ. 22	-	-	-	typ. -42

V _{CESM}	max.	65 V
V _{CEO}	max.	36 V
V _{EBO}	max.	4 V
I _{C(AV)}	max.	4 A
I _{CM}	max.	12 A
P _{rf}	max.	105 W
T _{stg}		-65 to + 150 °C
T _j	max.	200 °C

Drawings:



PINNING - SOT123

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

Fig.1 Simplified outline and symbol.